

IN THE SPECIFICATION

Please rewrite the paragraph beginning on page 14, line 25, and ending on page 15, line 3, as follows:

B1 The extrinsic base region 28, emitter region 26 and collector contact region 32 are provided with a base electrode 34, an emitter electrode 36 and a collector electrode 38, respectively.

Please rewrite the paragraph on page 15, lines 15-19, as follows:

B2 Each of the nMOSFET 14 and the pMOSFET 16 has a known LDD (lightly doped drain) structure and is formed in the device area isolated from the device area for the NPN bipolar transistor 12 by the first and second isolation trenches 20a and 20b.

IN THE CLAIMS

Please rewrite claim 1 as follows:

- Sub C
- B3
1. (Twice Amended) A semiconductor device comprising a silicon substrate, and a bipolar transistor having a collector well having a first conductivity-type, an internal base region having a second conductivity-type and received in said collector well and an emitter region having said first conductivity-type and received in said internal base region, a first annular isolation trench encircling said collector well, a second annular isolation trench encircling said first annular isolation trench, and an annular diffused region having said second conductivity-type disposed between said first annular isolation trench and said second annular isolation trench while being in contact with said first and second annular